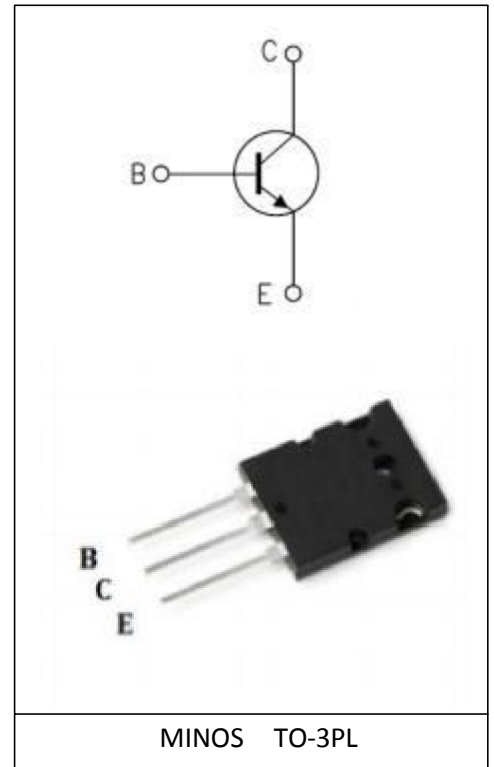


## Minos High Power Products NPN TRANSISTORS

### Features:

- ① Power Amplifier Applications
- ② Complementary to 2SC5200
- ③ High collector voltage:  $V_{CEO}=230V$  (min)
- ④ Recommended for 100-W high-fidelity audio frequency amplifier Output stage

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



### Absolute Maximum Ratings (Tc=25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		$V_{CBO}$	-230	V
Collector-emitter voltage		$V_{CEO}$	-230	V
Emitter-base voltage		$V_{EBO}$	-7	V
Collector current		$I_C$	-17	A
Base current		$I_B$	-5	A
Collector power dissipation	Tc=25°C	$P_C$	180	W
Junction temperature		$T_j$	150	°C
Storage temperature range		$T_{STG}$	-55~150	°C

### Package Marking And Ordering Information:

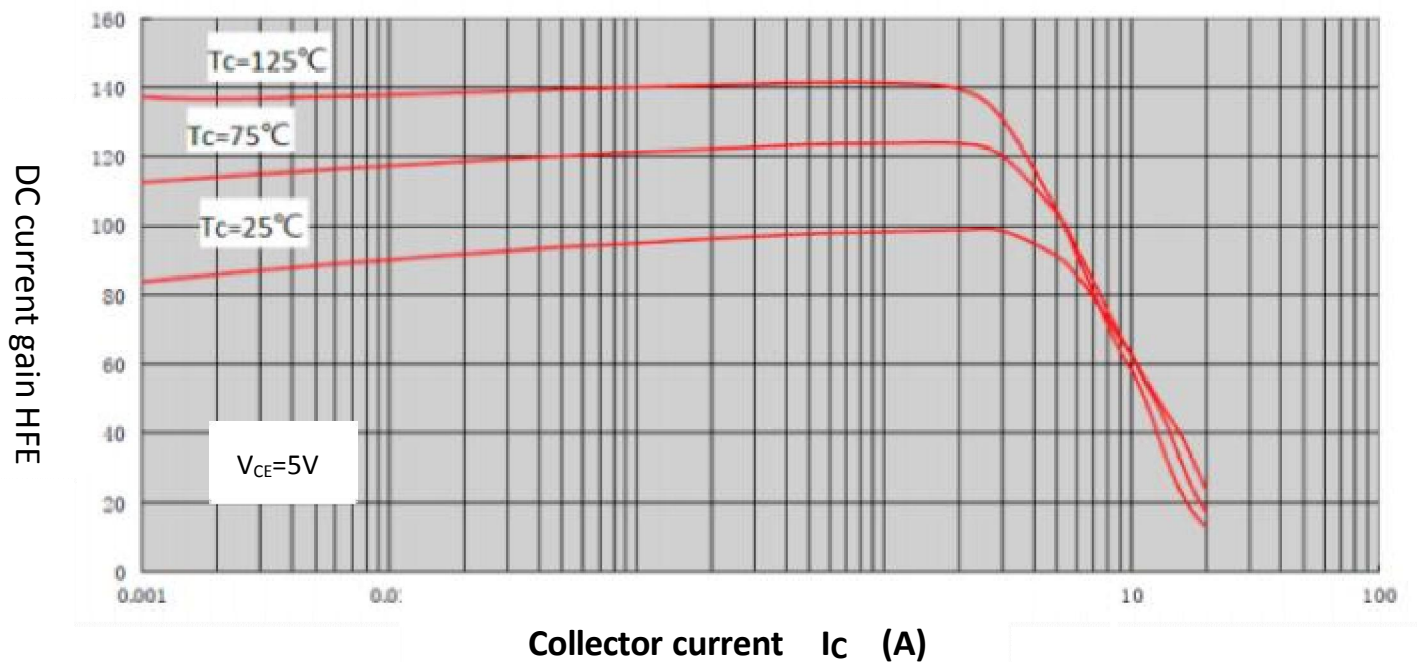
Ordering Codes	Package	Product Code	Packing
2SA1943	TO-3PL	1943	Tube

Electrical Characteristics  $T_c = (25^\circ\text{C})$

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = -230V; I_E = 0$			-500	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -7V; I_C = 0$			-500	$\mu A$
Dc current gain	$h_{FE}$	$I_C = -5A; V_{CE} = -4V;$	70		140	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -4A; I_B = -0.4A$			-0.5	V
Transition frequency	$f_T$	$V_{CE} = -10V; I_{CE} = -0.5A; f = 1MHz$		28		MHZ
Symbol	Parameter	Typ		Units		
$R_{\theta JC}$	Junction-to-Case	0.68		$^\circ C/W$		

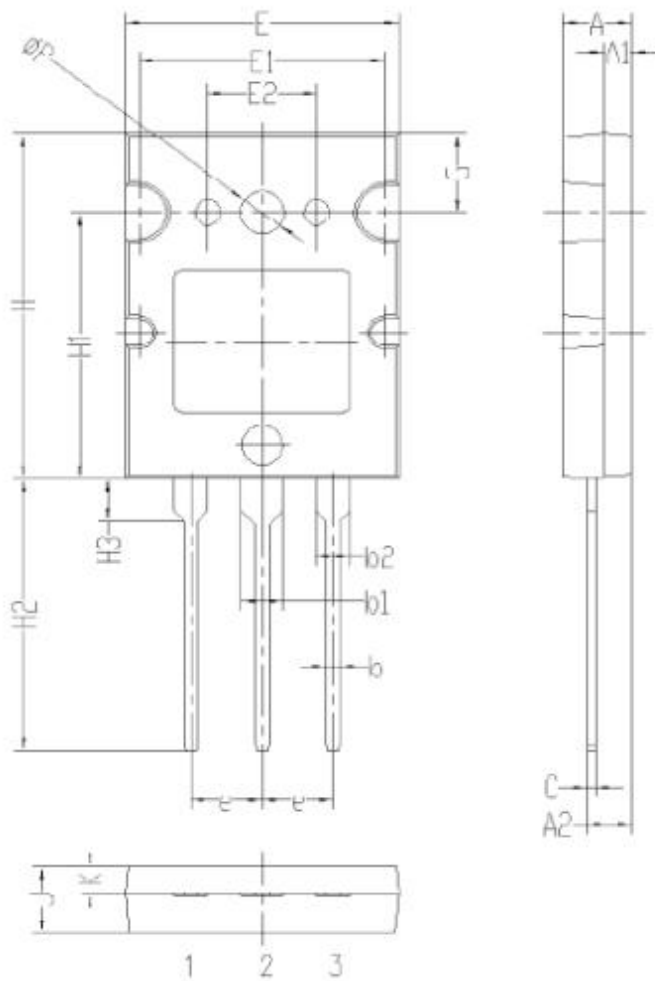
TYPICAL CHARACTERISTICS

HFE-- $I_C$



Package Information

TO-3PL PACKAGE



	单位 mm		
	MIN	NOM	MAX
A	4.8	5	5.2
A'	1.8	2	2.2
A2	3	3.2	3.4
b	0.8	1	1.2
b1	2.8	3	3.2
b2	2.3	2.5	2.7
c	0.4	0.6	0.8
e	5.25	5.45	5.65
E	19.8	20	20.2
E1	17.8	18	18.2
E2	7.8	8	8.2
H	25.8	26	26.2
H1	19.8	20	20.2
H2	20	20.5	21
H3	3.05	3.25	3.45
G	5.8	6	6.2
$\phi P$	3.1	3.3	3.5
J	4.8	5	5.2
K	1.8	2	2.2

**NOTE:**

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

**CONTACT:**

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